

General Description

The AOD421 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for load switching. It is ESD protected.

Features

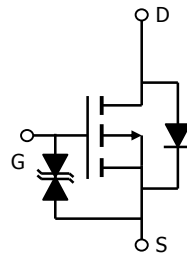
$$V_{DS} (V) = -20V$$

$$I_D = -12.5 A (V_{GS} = -10V)$$

$$R_{DS(ON)} < 75m\Omega (V_{GS} = -10V)$$

$$R_{DS(ON)} < 95m\Omega (V_{GS} = -4.5V)$$

$$R_{DS(ON)} < 145m\Omega (V_{GS} = -2.5V)$$



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^G	$T_A=25^\circ\text{C}$	-12.5	A
	$T_A=70^\circ\text{C}$	-8.9	
Pulsed Drain Current ^C	I_{DM}	-30	
Power Dissipation ^B	$T_C=25^\circ\text{C}$	18.8	W
	$T_C=100^\circ\text{C}$	9.4	
Power Dissipation ^A	$T_A=25^\circ\text{C}$	2	W
	$T_A=70^\circ\text{C}$	1.33	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	23	28	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient ^A		Steady-State	50	60
Maximum Junction-to-Case ^B	$R_{\theta JC}$	6	8	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}$, $V_{GS}=0\text{V}$			-0.5	μA
		$T_J=55^\circ\text{C}$			-2.5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 10\text{V}$			± 1	μA
		$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-0.7	-0.9	-1.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}$, $V_{DS}=-5\text{V}$	-15			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-12.5\text{A}$		61	75	$\text{m}\Omega$
		$T_J=125^\circ\text{C}$		83	105	
		$V_{GS}=-4.5\text{V}$, $I_D=-3\text{A}$		75	95	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$, $I_D=-1\text{A}$		110	145	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-12.5\text{A}$		8.8		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$	-1	-0.81		V
I_S	Maximum Body-Diode Continuous Current				-8.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-10\text{V}$, $f=1\text{MHz}$		512	620	pF
C_{oss}	Output Capacitance			77		pF
C_{riss}	Reverse Transfer Capacitance			62		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		9.2	13	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=-4.5\text{V}$, $V_{DS}=-10\text{V}$, $I_D=-12.5\text{A}$		4.6		nC
Q_{gs}	Gate Source Charge			0.9		nC
Q_{gd}	Gate Drain Charge			2.1		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$, $V_{DS}=-10\text{V}$, $R_L=0.75\Omega$, $R_{GEN}=3\Omega$		5.2		ns
t_r	Turn-On Rise Time			38		ns
$t_{D(off)}$	Turn-Off DelayTime			17		ns
t_f	Turn-Off Fall Time			31		ns
t_{rr}	Body Diode Reverse Recovery Time		$I_F=-12.5\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		19	
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-12.5\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		6.3		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B: The power dissipation P_D is based on $T_{J(MAX)}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=175^\circ\text{C}$.

D: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=175^\circ\text{C}$.

G: The maximum current rating is limited by bond-wires.

H: These tests are performed with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

*This device is guaranteed green after data code 8X11 (Sep 1ST 2008).

Rev 1: Sep 2008

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

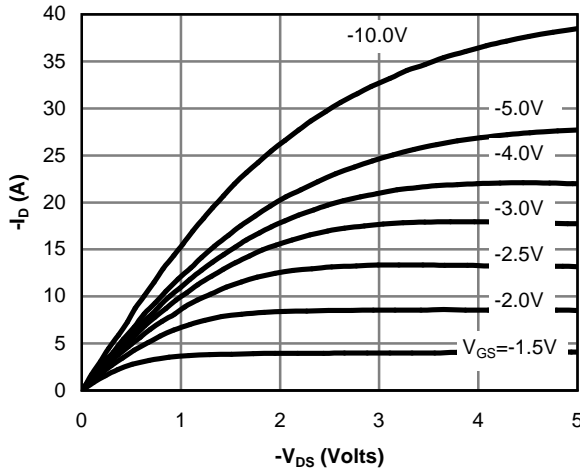


Figure 1: On-Region Characteristics

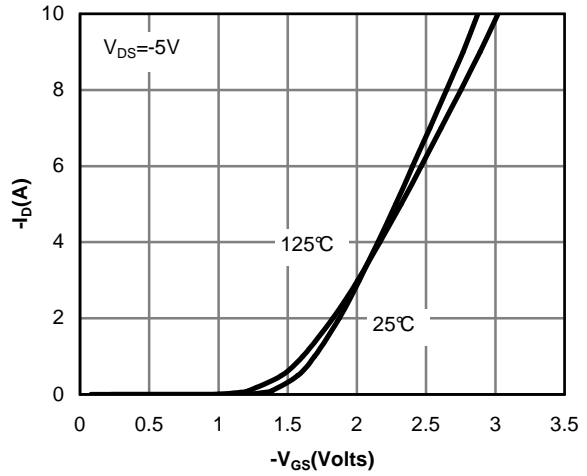


Figure 2: Transfer Characteristics

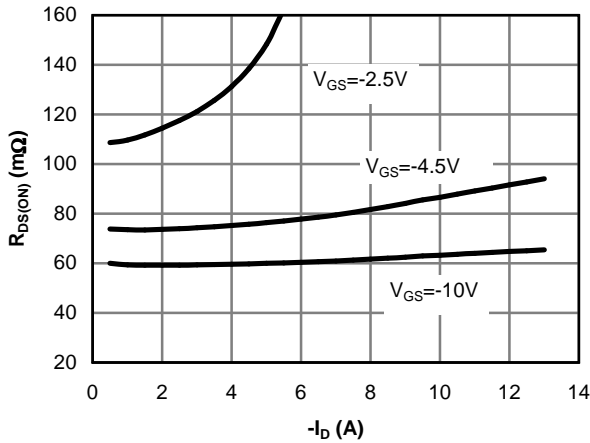


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

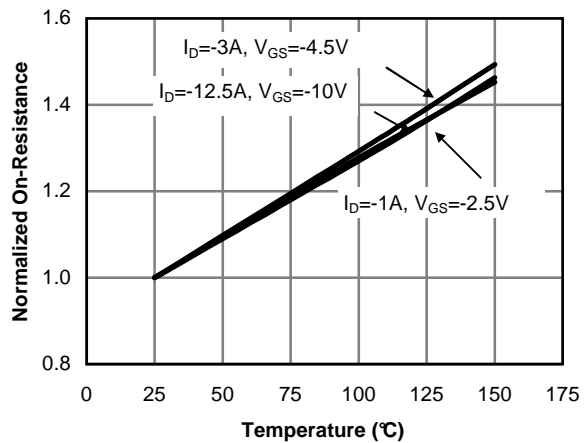


Figure 4: On-Resistance vs. Junction Temperature

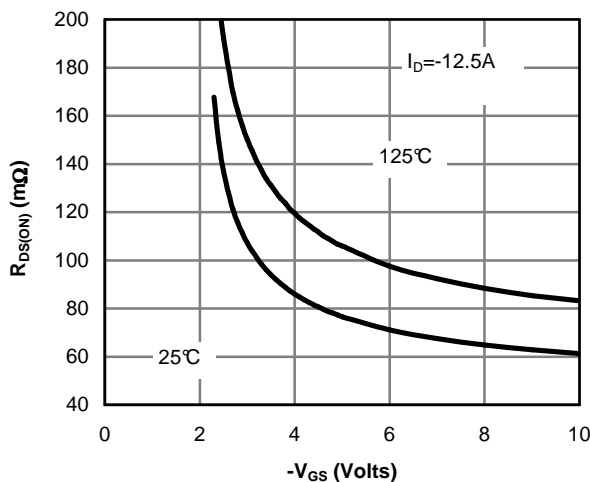


Figure 5: On-Resistance vs. Gate-Source Voltage

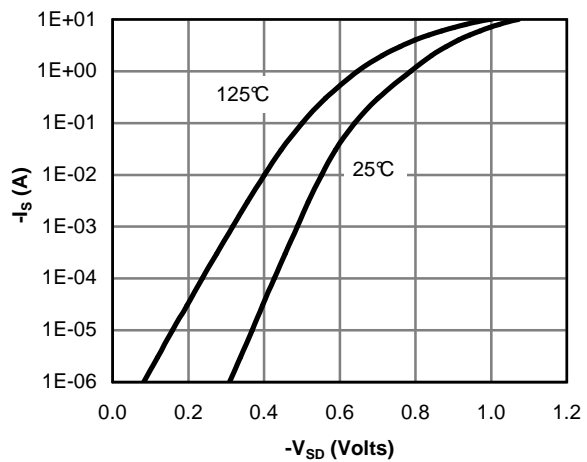


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

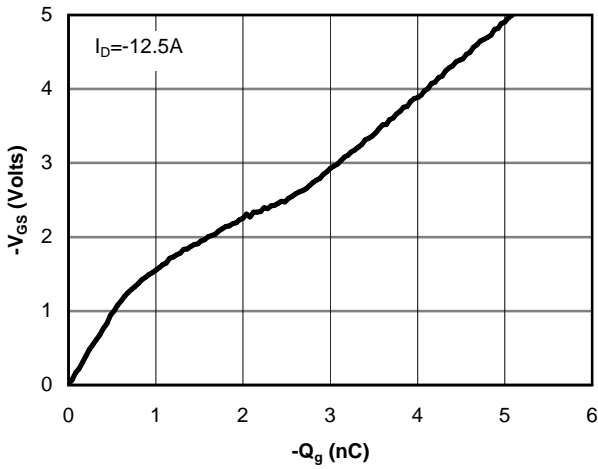


Figure 7: Gate-Charge Characteristics

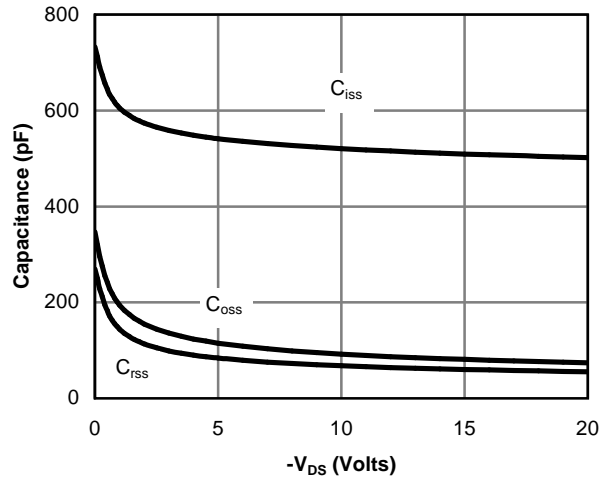


Figure 8: Capacitance Characteristics

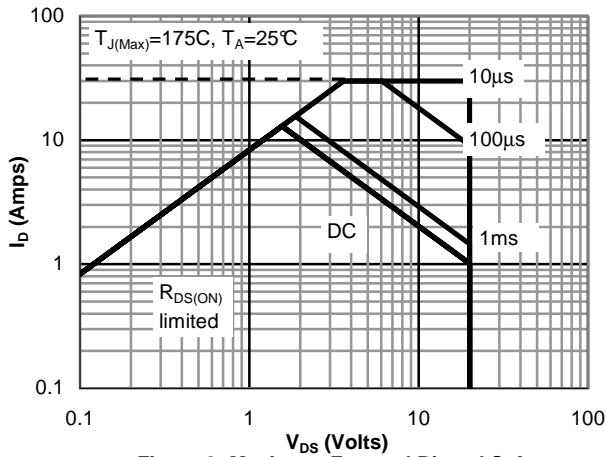


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

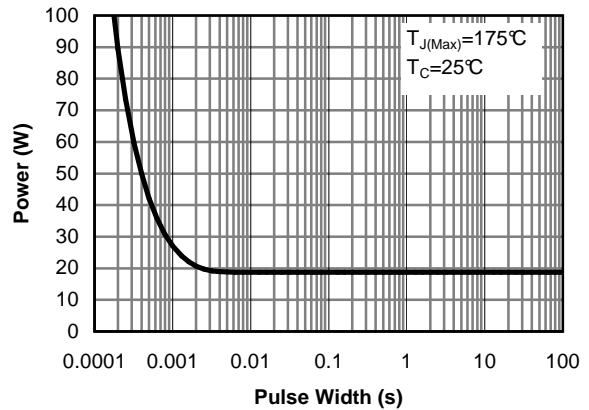


Figure 10: Single Pulse Power Rating Junction-to-case (Note F)

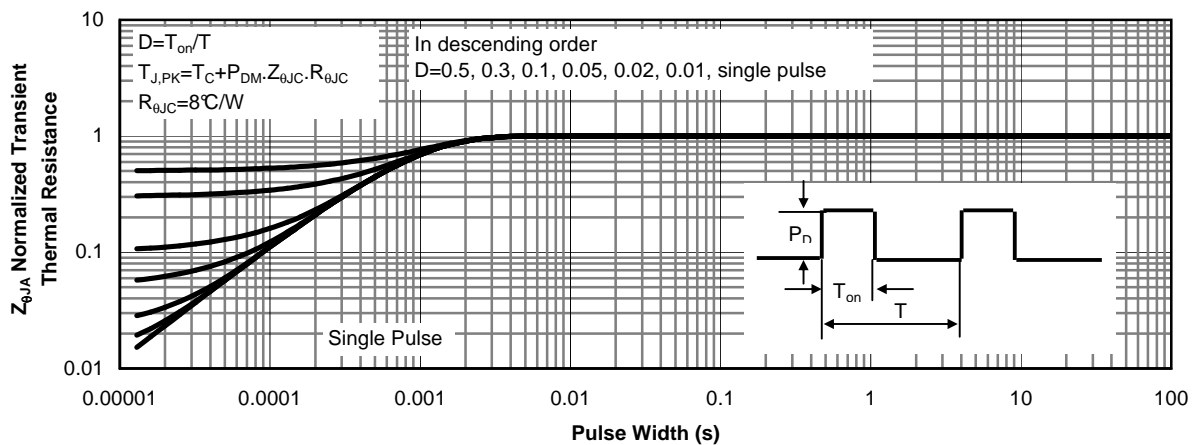


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

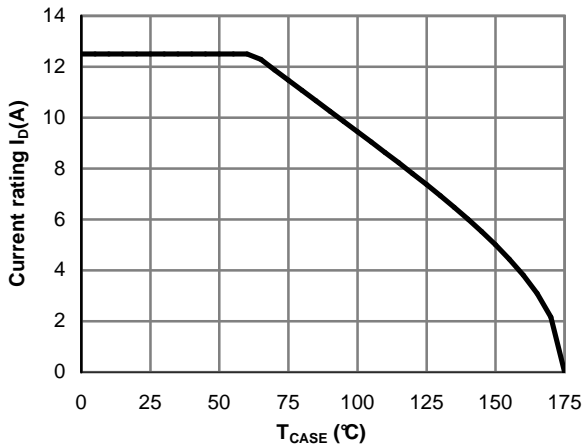


Figure 12: Current De-rating (Note B)

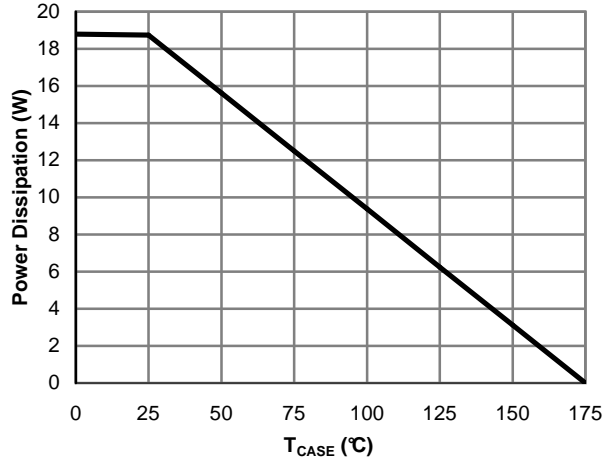


Figure 13: Power De-rating (Note B)

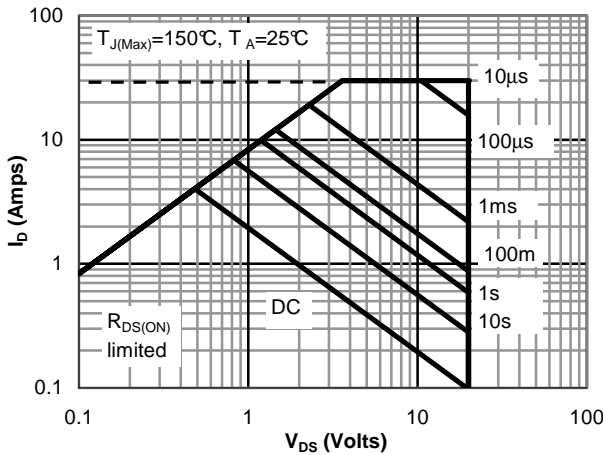


Figure 14: Maximum Forward Biased Safe Operating Area (Note H)

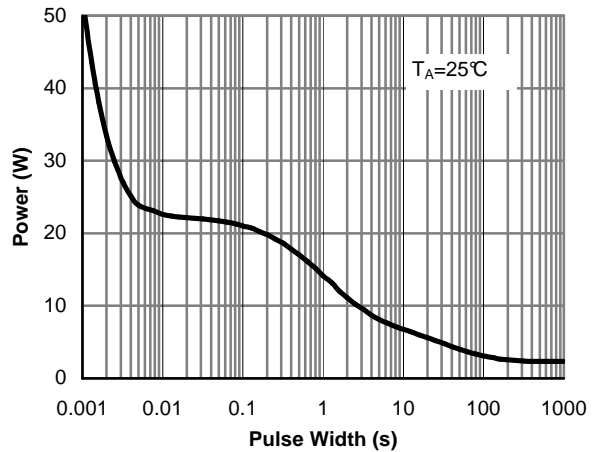


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

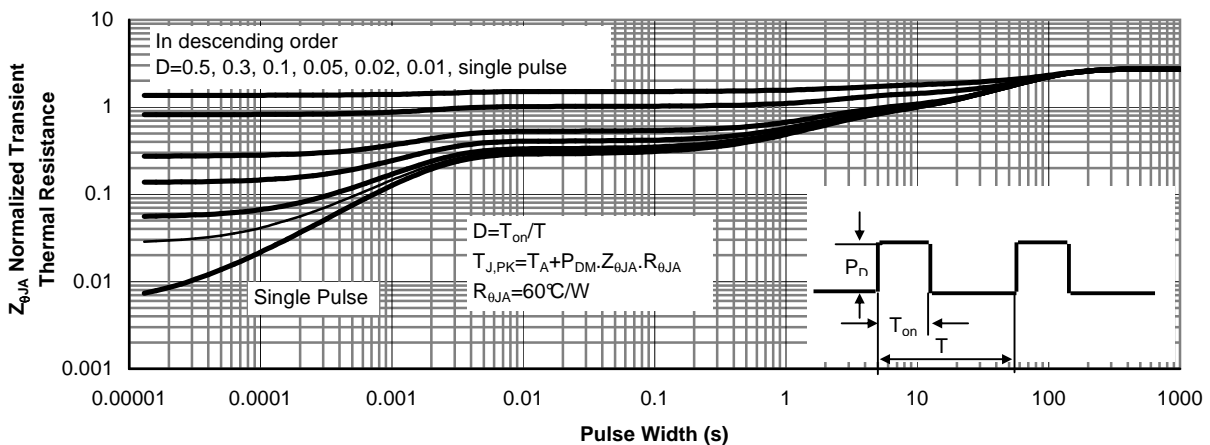
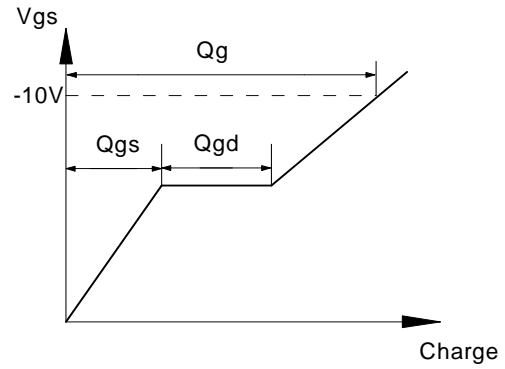
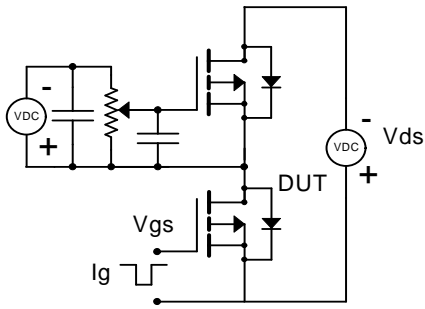
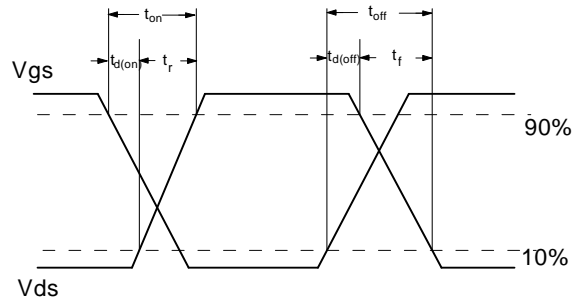
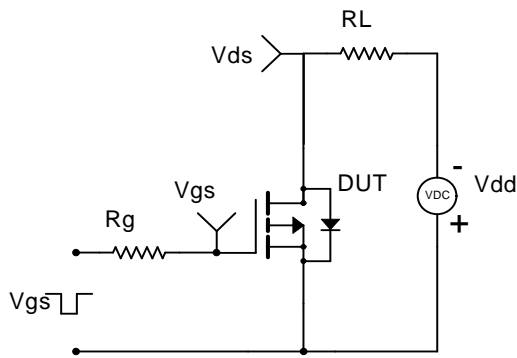


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

